



**Mechanical date:**  $A_x=A_y=230\mu\text{m}$   
 $B_x=B_y=85\mu\text{m}$

**Schematic and pinning diagram**

**Chip thickness:**  $635 \pm 20\mu\text{m}$

**Scribe Line width** -  $60\mu\text{m}$ .

**Top Metal:** Al – for wire bonding,  $d=2.2\pm 0.2\mu\text{m}$

**Back side** : without metallization

**Top Side** - pin 1, **Back Side** - pin 2.

**Probing: sampling testing:** no bad dice inking, guaranteed good dice quantity  $\geq 95\%$ .

### Limiting values

Parameter	Symbol	Conditions	Value	Unit
Reverse Stand-off voltage	$V_{RWM}$	-	5	V
Peak Pulse Power	$P_{PP}$	$t_p=8/20\mu\text{s}$	35*	W
Peak Pulse Current	$I_{PP}$	$t_p=8/20\mu\text{s}$	2*	A
Electrostatic Discharge	$V_{ESD}$	IEC 61000-4-2, level 4.	+/-8 (Contact); +/-15 (Air).	kV
Max.junction temperature	$T_j$	-	+150	$^{\circ}\text{C}$

### Characteristics ( $T_a=25^{\circ}\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_R$	Diode reverse leakage current.	$V=\pm 5,0\text{ V}$	-	-	90	nA
$V_{BR}$	Breakdown voltage. Pin 1 to 2 or Pin2 to 1.	$I_R=1\text{mA}$	5,6	-	9,4	V
$C_j$	Diode capacitance .	$F=1\text{MHz}$ , $V_{dc}=0\text{ V}$ .	-	3,0	3,5	pF
$V_{CL}$	lamping voltage	$I_{pp}=1,0\text{A}$ ; $I_{pp}= 2,0\text{A}$ ; $t_p= 8/20\mu\text{S}$ .	-	-	10,0* 13,0*	V

\*- For Device testing